Exposed



#### HIGH POWER LINEAR AMPLIFIER

### Typical Applications

- PCS Communication Systems
- Digital Communication Systems
- DECT Cordless Applications

- Commercial and Consumer Systems
- Portable Battery-Powered Equipment

### **Product Description**

The RF2125P is a high power, high efficiency linear amplifier IC. The device is manufactured on an advanced Gallium Arsenide Heterojunction Bipolar Transistor (HBT) process and has been designed for use as the final RF amplifier in digital PCS phone transmitters and base stations requiring linear amplification operating between 1500MHz and 2200MHz. It will also function as a high efficiency amplifier for constant envelope applications such as DECT. The device is packaged in an 8-lead plastic package with a backside ground. The device is self-contained with the exception of the output matching network and power supply feed line. It produces a typical output power level of 1 W.

0.05 П 2.70  $\neg$ 6.00 ± 0.20 ± 0.10 1.70 Dimensions in mm. 8° MAX 0° MIN  $\pm 0.03$ NOTES: 1. Shaded lead is pin 1 0.60 2. Lead coplanarity - 0.10 with respect to datum "A".

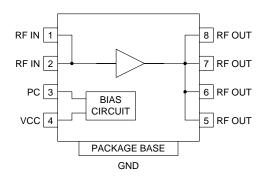
Optimum Technology Matching® Applied

Si BJT

▼ GaAs HBT

GaAs MESFET

☐ Si Bi-CMOS ☐ SiGe HBT ☐ Si CMOS



Functional Block Diagram

#### Package Style: SOIC-8 Slug

### **Features**

- Single 2.7V to 7.5V Supply
- 1W Output Power

3.90

- 14dB Gain
- 45% Efficiency
- Power Down Mode
- 1500MHz to 2200MHz Operation

### Ordering Information

RF2125P High Power Linear Amplifier
RF2125P PCBA Fully Assembled Evaluation Board

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## RF2125P

### **Absolute Maximum Ratings**

Parameter	Rating	Unit
Supply Voltage (V <sub>CC</sub> )	-0.5 to +7.5	$V_{DC}$
Power Control Voltage (V <sub>PC</sub> )	-0.5 to +5 V	V
DC Supply Current	450	mA
Input RF Power	+20	dBm
Output Load VSWR	20:1	
Operating Ambient Temperature	-40 to +85	°C
Storage Temperature	-40 to +100	°C

Refer to "Handling of PSOP and PSSOP Products" on page 16-15 for special handling information.



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Parameter	Specification		Unit	Condition		
Parameter	Min.	Тур.	Max.	Unit	Condition	
Overall					T=25 °C, $V_{CC}$ =6.0V, $V_{PC}$ =5.0V, $Z_{LOAD}$ =12 $\Omega$ , $P_{in}$ = 0dBm, Freq=1885MHz, Idle current=180mA	
Frequency Range		1500 to 2200		MHz		
Maximum Output Power		+28.5		dBm	$V_{CC}$ =3.6V, $P_{IN}$ =+17dBm	
Maximum Output Power		+29.5		dBm	V <sub>CC</sub> =4.8 V, P <sub>IN</sub> =+17dBm	
Maximum Output Power	+29.0	+30		dBm	V <sub>CC</sub> =6.0 V, P <sub>IN</sub> =+17dBm	
Total Power Added Efficiency		45		%	Maximum output, V <sub>CC</sub> =3.6V	
Total Power Added Efficiency		45		%	Maximum output, V <sub>CC</sub> =4.8V	
Total Power Added Efficiency	40	45		%	Maximum output, V <sub>CC</sub> =6.0V	
Small-signal Gain	12	14		dB		
Second Harmonic		-40		dBc		
Third Harmonic		-45		dBc		
Fourth Harmonic		-35		dBc		
Isolation		15		dB	V <sub>PC</sub> =0.2V	
Input VSWR		1.5:1			With external matching network; see application schematic	
Two-tone Specification						
Average Two-Tone Power		+27		dBm	PEP-3dB	
IM <sub>3</sub>	-23	-30		dBc	P <sub>OUT</sub> =+24dBm for each tone	
IM <sub>5</sub>		-35		dBc	P <sub>OUT</sub> =+24dBm for each tone	
IM <sub>7</sub>		-45		dBc	P <sub>OUT</sub> =+24dBm for each tone	
Power Control						
V <sub>PC</sub>	1.5	3.3	3.5	V	To obtain 180mA idle current	
PC Current		1		mA	V <sub>PC</sub> =2.0V	
		2		mA	$V_{PC}=3.5V$	
Power Control "OFF"	0.2	0.5		V	Threshold voltage at device input	
Power Supply						
Power Supply voltage		2.7 to 7.5		V		
Supply Current	200	360	500	mA	$P_{OUT}$ =+30dBm, $V_{CC}$ =6.0V	
Power Down Current		0.5	10	μΑ	V <sub>PC</sub> =0.2V	

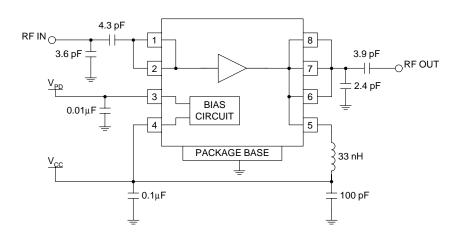
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Pin	Function	Description	Interface Schematic
1	RF IN	RF input. This input is DC coupled, so an external blocking capacitor is required if this pin is connected to a DC path. An optimum match to $50\Omega$ is obtained by providing an external series capacitor of 4.3pF and then a shunt capacitor of 3.3pF; see the application schematic. Those values are typical for 1880MHz; other values may be required for other frequencies.	
2	RF IN	Same as pin 1.	
3	PC	Power control pin. For obtaining maximum performance the voltage on this pin can be used to set correct bias level. In a typical application this is implemented by a feedback loop. The feedback can be based on the actual supply current of the device, i.e. maintaining a fixed current level, or it can be based on the RF output power level to maintain a fixed RF power level (Automatic Level Control loop). A voltage of 0.5 V or lower brings the part into power down state.	
4	VCC	Power supply pin for the bias circuits. External low frequency bypass capacitors should be connected if no other low frequency decoupling is nearby.	
5	RF OUT	RF output and bias for the output stage. The power supply for the output transistor needs to be supplied to this pin. This can be done through a quarter wave length microstrip line that is RF grounded at the other end, or through an RF inductor that supports the required DC currents. Optimum load impedance is achieved by providing a shunt capacitor of 3.0pF and a series capacitor of 3.9pF; see the application schematic. Those values are typical for 1880MHz; other values may be required for other frequencies. Since there are several output pins available, which are internally connected, one pin can be used for connecting the bias, another for connecting a (third) harmonic trap filter, and the other pins for the RF output.	
6	RF OUT	Same as pin 5.	
7	RF OUT	Same as pin 5.	
8	RF OUT	Same as pin 5.	
Pkg Base	GND	Ground connection. The backside of the package should be connected to the ground plane through a short path, i.e., vias under the device may be required.	

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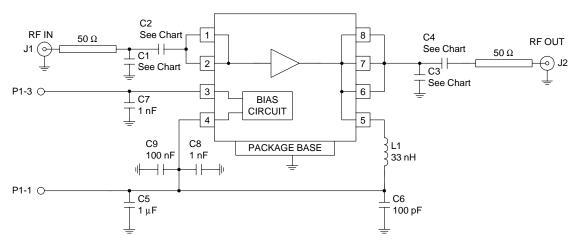
## Application Schematic 1880MHz Operation

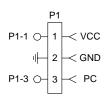


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### **Evaluation Board Schematic**

(Download Bill of Materials from www.rfmd.com.)





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Capacitors are ATC type.
The 2.7 pF capacitor is 2.4 pF in parallel with 0.3 pF.

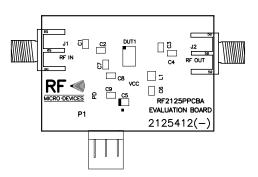
APPLICATION	C1 (pF)	C2 (pF)	C3 (pF)	C4 (pF)
DCS1800 (1710 to 1785 MHz)	3.3	7.5	3.6	3.9
DECT (1880 to 1990 MHz)	3.0	3.9	2.7	3.6
Broadband and Unlicensed PCS (1850 to 1910 MHz)	3.6	4.3	2.4	3.9
Broadband and Unlicensed PCS (1910 to 1970 MHz)	3.0	3.9	2.7	3.6

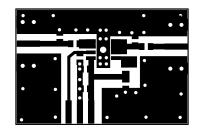
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## **Evaluation Board Layout**

1.0" x 1.5"

Board Thickness 0.031"; Board Material FR-4





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